

CD4011B, CD4012B, CD4023B Types

CMOS NAND GATES

High-Voltage Types (20-Volt Rating)

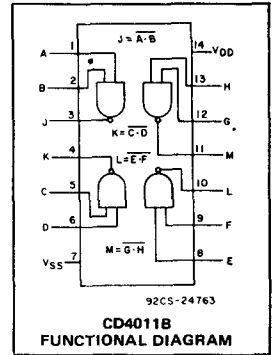
Quad 2 Input – CD4011B
Dual 4 Input – CD4012B
Triple 3 Input – CD4023B

RCA-CD4011B, CD4012B, and CD4023B NAND gates provide the system designer with direct implementation of the NAND function and supplement the existing family of CMOS gates. All inputs and outputs are buffered.

The CD4011B, CD4012B, and CD4023B types are supplied in 14-lead hermetic dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), 14-lead ceramic flat packages (K suffix), and in chip form (H suffix).

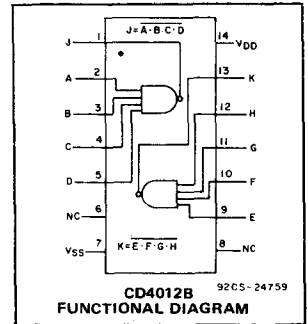
Features:

- Propagation delay time = 60 ns (typ.) at $C_L = 50$ pF, $V_{DD} = 10$ V
- Buffered inputs and outputs
- Standardized symmetrical output characteristics
- Maximum input current of 1 μ A at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- 100% tested for quiescent current at 20 V
- 5-V, 10-V, and 15-V parametric ratings
- Noise margin (over full package temperature range):
 - 1 V at $V_{DD} = 5$ V
 - 2 V at $V_{DD} = 10$ V
 - 2.5 V at $V_{DD} = 15$ V
- Meets all requirements of JEDEC Tentative Standard No.13A, "Standard Specifications for Description of "B" Series CMOS Devices"



MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V_{DD}) (Voltages referenced to V_{SS} Terminal)	-0.5 to +20 V
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5 to $V_{DD} + 0.5$ V
DC INPUT CURRENT, ANY ONE INPUT	± 10 mA
POWER DISSIPATION PER PACKAGE (P_D):	
For $T_A = -40$ to $+60^\circ\text{C}$ (PACKAGE TYPE E)	500 mW
For $T_A = +60$ to $+85^\circ\text{C}$ (PACKAGE TYPE E)	Derate Linearly at 12 mW/ $^\circ\text{C}$ to 200 mW
For $T_A = -55$ to $+100^\circ\text{C}$ (PACKAGE TYPES D, F, K)	500 mW
For $T_A = +100$ to $+125^\circ\text{C}$ (PACKAGE TYPES D, F, K)	Derate Linearly at 12 mW/ $^\circ\text{C}$ to 200 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR $T_A =$ FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100 mW
OPERATING-TEMPERATURE RANGE (T_A):	
PACKAGE TYPES D, F, K, H	-55 to $+125^\circ\text{C}$
PACKAGE TYPE E	-40 to $+85^\circ\text{C}$
STORAGE TEMPERATURE RANGE (T_{stg})	-65 to $+150^\circ\text{C}$
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 inch (1.59 \pm 0.79 mm) from case for 10 s max.	$+265^\circ\text{C}$

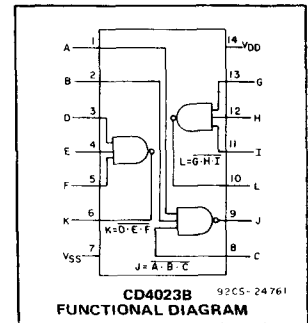
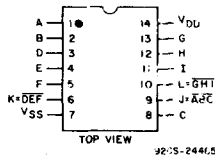
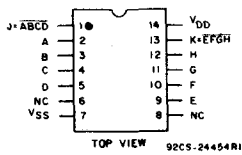
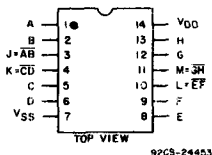


RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For $T_A =$ Full Package Temperature Range)	3	18	V

TERMINAL ASSIGNMENTS



CD4011B, CD4012B, CD4023B Types

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
	V _O (V)	V _{IN} (V)	V _{DD} (V)	Values at -55, +25, +125 Apply to D, F, K, H Packages Values at -40, +25, +85 Apply to E Package							
				-55	-40	+85	+125	+25		Max.	
				Min.	Typ.						
Quiescent Device Current, I _{DD} Max.	-	0,5	5	0.25	0.25	7.5	7.5	-	0.01	0.25	μA
	-	0,10	10	0.5	0.5	15	15	-	0.01	0.5	
	-	0,15	15	1	1	30	30	-	0.01	1	
Output Low (Sink) Current I _{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	-	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	-	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	-	
Output High (Source) Current, I _{OH} Min.	4.6	0,5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	-	mA
	2.5	0,5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	-	
	9.5	0,10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	-	
	13.5	0,15	15	-4.2	-4	-2.8	-2.4	-3.4	-6.8	-	
Output Voltage: Low-Level, V _{OL} Max.	-	0,5	5	0.05				-	0	0.05	V
	-	0,10	10	0.05				-	0	0.05	
	-	0,15	15	0.05				-	0	0.05	
Output Voltage: High-Level, V _{OH} Min.	-	0,5	5	4.95				4.95	5	-	V
	-	0,10	10	9.95				9.95	10	-	
	-	0,15	15	14.95				14.95	15	-	
Input Low Voltage, V _{IL} Max.	4.5	-	5	1.5				-	-	1.5	V
	9	-	10	3				-	-	3	
	13.5	-	15	4				-	-	4	
Input High Voltage, V _{IH} Min.	0.5,4.5	-	5	3.5				3.5	-	-	V
	1.9	-	10	7				7	-	-	
	1.5,13.5	-	15	11				11	-	-	
Input Current I _{IN} Max.		0,18	18	±0.1	±0.1	±1	±1	-	±10 ⁻⁵	±0.1	μA

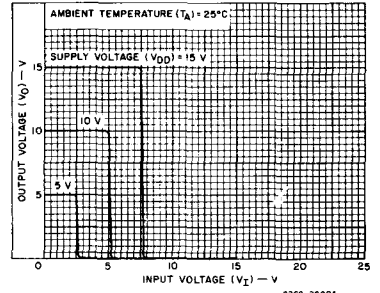


Fig. 1 - Typical voltage transfer characteristics.

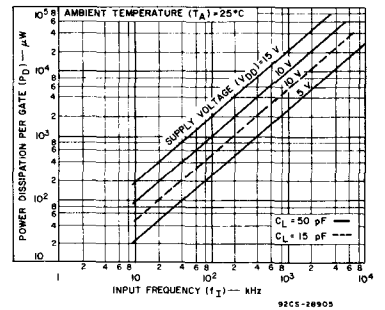


Fig. 2 - Typical power dissipation characteristics.

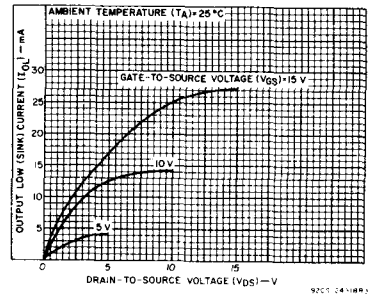


Fig. 3 - Typical output low (sink) current characteristics.

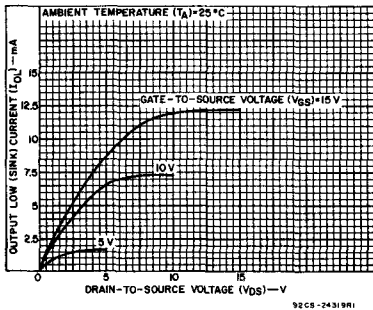


Fig. 4 - Minimum output low (sink) current characteristics.

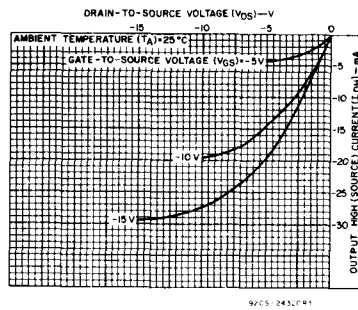


Fig. 5 - Typical output high (source) current characteristics.

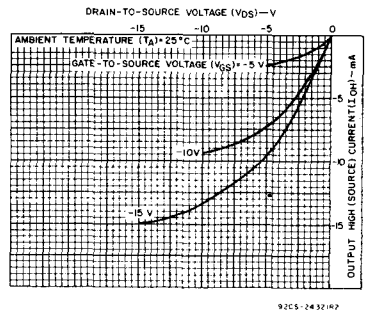
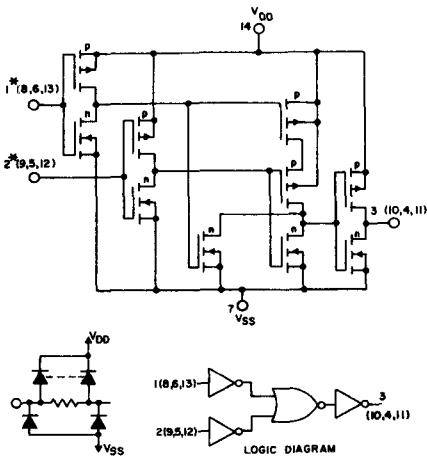


Fig. 6 - Minimum output high (source) current characteristics.

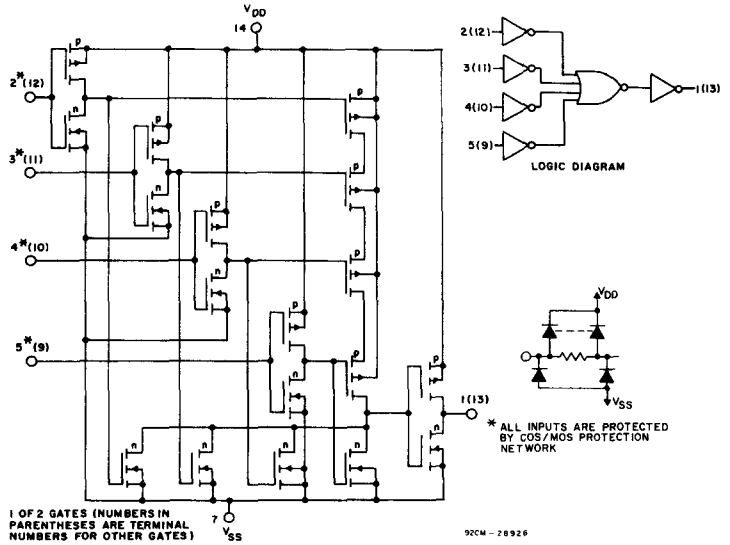
CD4011B, CD4012B, CD4023B Types



* ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

1 OF 4 GATES (NUMBERS IN PARENTHESES ARE TERMINAL NUMBERS FOR OTHER GATES)

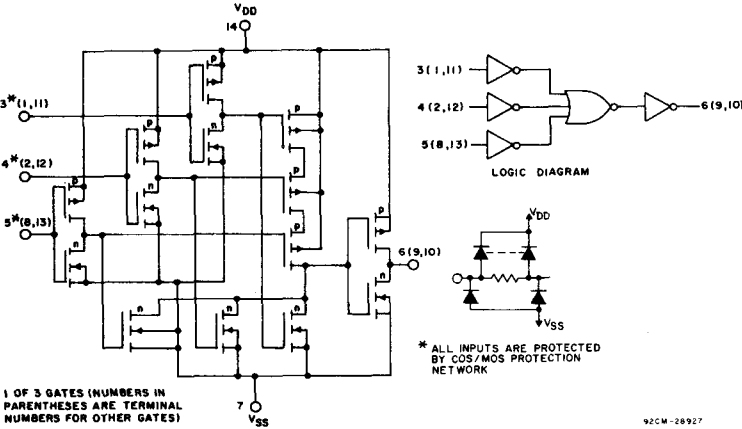
Fig. 7 - Schematic and logic diagrams for CD4011B.



1 OF 2 GATES (NUMBERS IN PARENTHESES ARE TERMINAL NUMBERS FOR OTHER GATES)

92CM-28926

Fig. 8 - Schematic and logic diagrams for CD4012B.



1 OF 3 GATES (NUMBERS IN PARENTHESES ARE TERMINAL NUMBERS FOR OTHER GATES)

* ALL INPUTS ARE PROTECTED BY COS/MOS PROTECTION NETWORK

92CM-28927

Fig. 9 - Schematic and logic diagrams for CD4023B.

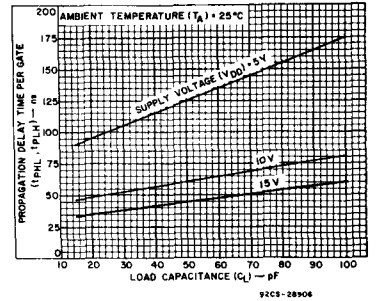


Fig. 10 - Typical propagation delay time per gate as a function of load capacitance.

DYNAMIC ELECTRICAL CHARACTERISTICS

At $T_A = 25^\circ\text{C}$; Input $t_r, t_f = 20\text{ ns}$, $C_L = 50\text{ pF}$, $R_L = 200\text{ k}\Omega$

CHARACTERISTIC	TEST CONDITIONS	ALL TYPES LIMITS		UNITS	
		V_{DD} VOLTS	TYP.		MAX.
Propagation Delay Time, t_{PHL}, t_{PLH}		5	125	250	ns
		10	60	120	
		15	45	90	
Transition Time, t_{THL}, t_{TLH}		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance, C_{iN}	Any Input		5	7.5	pF

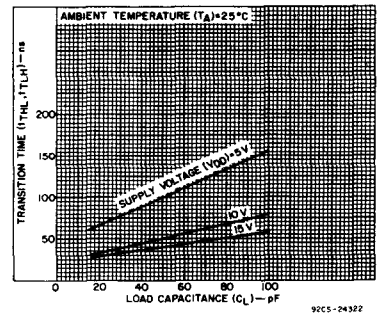


Fig. 11 - Typical transition time as a function of load capacitance.

CD4011B, CD4012B, CD4023B Types

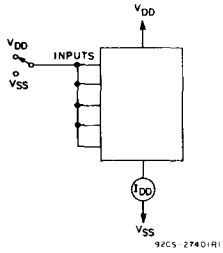


Fig. 12 - Quiescent-device-current test circuit.

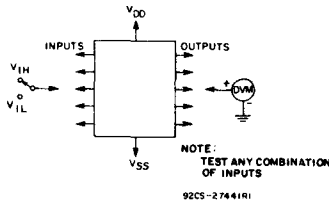


Fig. 13 - Input-voltage test circuit.

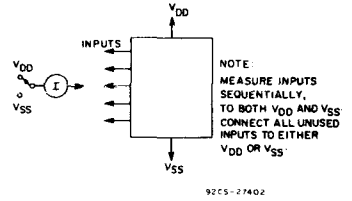
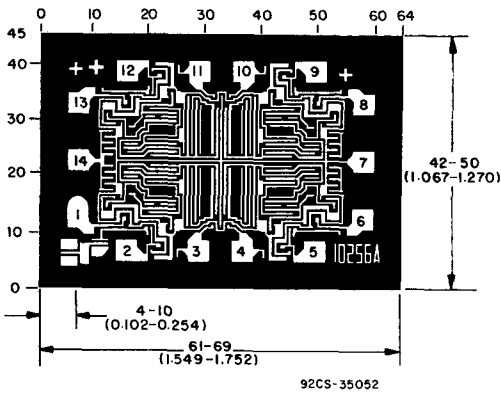
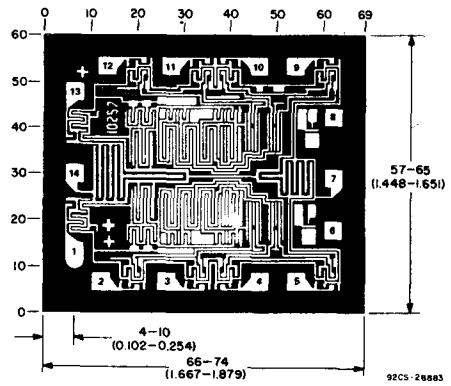


Fig. 14 - Input-current test circuit.

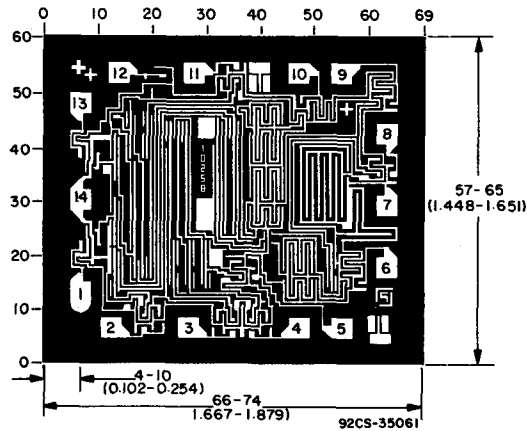
CHIP PHOTOGRAPHS Dimensions and Pad Layouts



CD4011BH



CD4012BH



CD4023BH

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).

The photographs and dimensions of each CMOS chip represent a chip when it is part of the wafer. When the wafer is separated into individual chips, the angle of cleavage may vary with respect to the chip face for different chips. The actual dimensions of the isolated chip, therefore, may differ slightly from the nominal dimensions shown. The user should consider a tolerance of -3 mils to $+16$ mils applicable to the nominal dimensions shown.